

Claim Amendments:

1-13. (Withdrawn)

14. (Currently Amended) A memory device having an accessible source such that device parameters can be determined, comprising:

a dimple ground into a back-side of a semiconductor substrate of the device;

a trench milled from the bottom portion of the dimple exposing a portion of a vertical trench fill; and

a conductive material connecting the vertical trench fill and a buried plate of the device, wherein the conductive material is a layer covering a portion of the back-side of the semiconductor substrate.

15. (Previously Amended) The system of claim 14, wherein the trench is milled into a portion of the vertical trench fill and the buried plate.

16. (Previously Amended) The system of claim 14, wherein the conductive material is a back-side electrode.

17. (Cancelled)

18. (Previously Amended) The system of claim 14, wherein a macro design of the memory device is substantially similar to a product line macro design.

19. (Previously Amended) The system of claim 18, wherein the memory device dimensions are substantially the same as those of the product line macro design.